NCV8440, NCV8440A

Protected Power MOSFET

2.6 A, 52 V, N−Channel, Logic Level, Clamped MOSFET w/ ESD Protection

Features

- Diode Clamp Between Gate and Source
- ESD Protection − Human Body Model 5000 V
- Active Over−Voltage Gate to Drain Clamp
- Scalable to Lower or Higher $R_{DS(on)}$
- Internal Series Gate Resistance
- These are Pb−Free Devices

Benefits

- High Energy Capability for Inductive Loads
- Low Switching Noise Generation

Applications

- Automotive and Industrial Markets:
  Solenoid Drivers, Lamp Drivers, Small Motor Drivers
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable

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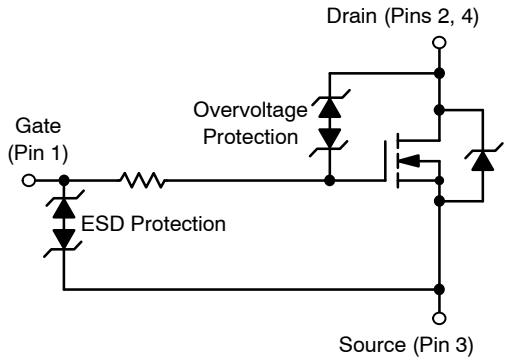
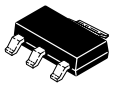
V_{DSS} (Clamped)	$R_{DS(ON)}$ TYP	I_D MAX
52 V	95 mΩ @ 10 V	2.6 A

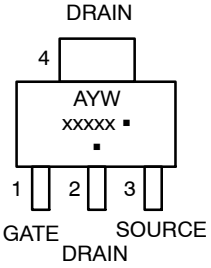




SOT−223
CASE 318E
STYLE 3

1 = Gate
2 = Drain
3 = Source

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
xxxxx = V8440 or 8440A
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage Internally Clamped	V_{DSS}	52−59	V
Gate−to−Source Voltage − Continuous	V_{GS}	±15	V
Drain Current − Continuous @ T_A = 25°C − Single Pulse (t_p = 10 μs) (Note 1)	I_D I_{DM}	 2.6 10	A
Total Power Dissipation @ T_A = 25°C (Note 1)	P_D	1.69	W
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 50 V, $I_{D(pk)}$ = 1.17 A, V_{GS} = 10 V, L = 160 mH, R_G = 25 Ω)	E_{AS}	110	mJ
Load Dump Voltage (V_{GS} = 0 and 10 V, R_I = 2.0 Ω, R_L = 9.0 Ω, td = 400 ms)	V_{LD}	60	V
Thermal Resistance, Junction−to−Ambient (Note 1) Junction−to−Ambient (Note 2)	 $R_{\theta JA}$ $R_{\theta JA}$	 74 169	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from Case for 10 Seconds	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted to a FR4 board using 1″ pad size, (Cu area 1.127 in^2).
2. When surface mounted to a FR4 board using minimum recommended pad size, (Cu area 0.412 in^2).

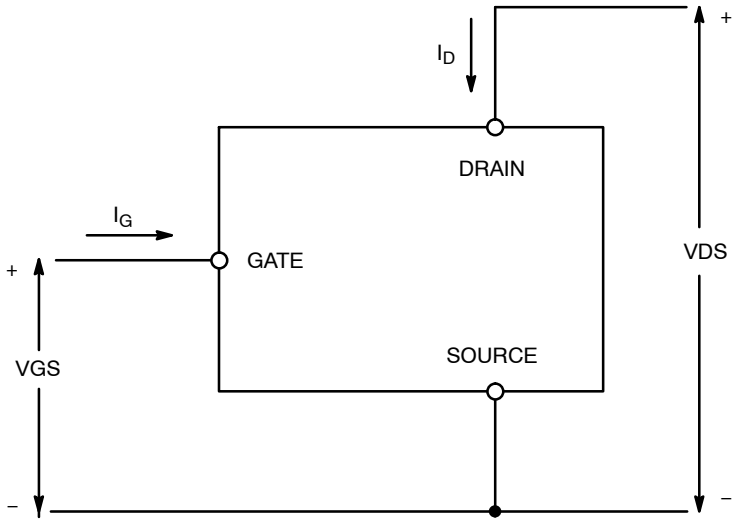


Figure 1. Voltage and Current Convention

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain−to−Source Breakdown Voltage (Note 3) (V_{GS} = 0 V, I_D = 1.0 mA, T_J = 25°C) (V_{GS} = 0 V, I_D = 1.0 mA, T_J = −40°C to 125°C) (Note 4) Temperature Coefficient (Negative)	$V_{(BR)DSS}$	 52 50.8	 55 54 −9.3	 59 59.5	 V V mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 40 V, V_{GS} = 0 V) (V_{DS} = 40 V, V_{GS} = 0 V, T_J = 125°C) (Note 4)	I_{DSS}			 10 25	μA
Gate−Body Leakage Current (V_{GS} = ±8 V, V_{DS} = 0 V) (V_{GS} = ±14 V, V_{DS} = 0 V)	I_{GSS}		 ±35	 ±10	μA
ON CHARACTERISTICS (Note 3)					
Gate Threshold Voltage (Note 3) (V_{DS} = V_{GS}, I_D = 100 μA) Threshold Temperature Coefficient (Negative)	$V_{GS(th)}$	1.1	1.5 −4.1	1.9	V mV/°C
Static Drain−to−Source On−Resistance (Note 3) (V_{GS} = 3.5 V, I_D = 0.6 A) (V_{GS} = 4.0 V, I_D = 1.5 A) (V_{GS} = 10 V, I_D = 2.6 A)	$R_{DS(on)}$		 150 135 95	 180 160 110	mΩ
Forward Transconductance (Note 3) (V_{DS} = 15 V, I_D = 2.6 A)	g_{FS}		3.8		Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	V_{DS} = 35 V, V_{GS} = 0 V, f = 10 kHz	C_{iss}		155		pF
Output Capacitance		C_{oss}		60		
Transfer Capacitance		C_{rss}		25		
Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 10 kHz	C_{iss}		170		pF
Output Capacitance		C_{oss}		70		
Transfer Capacitance		C_{rss}		30		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Not subject to production testing.
5. Switching characteristics are independent of operating junction temperatures.

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 5)						
Turn−On Delay Time	V_{GS} = 4.5 V, V_{DD} = 40 V, I_D = 2.6 A, R_D = 15.4 Ω	$t_{d(on)}$		375		ns
Rise Time		t_r		1525		
Turn−Off Delay Time		$t_{d(off)}$		1530		
Fall Time		t_f		1160		
Turn−On Delay Time	V_{GS} = 4.5 V, V_{DD} = 40 V, I_D = 1.0 A, R_D = 40 Ω	$t_{d(on)}$		325		ns
Rise Time		t_r		1275		
Turn−Off Delay Time		$t_{d(off)}$		1860		
Fall Time		t_f		1150		
Turn−On Delay Time	V_{GS} = 10 V, V_{DD} = 15 V, I_D = 2.6 A, R_D = 5.8 Ω	$t_{d(on)}$		190		ns
Rise Time		t_r		710		
Turn−Off Delay Time		$t_{d(off)}$		2220		
Fall Time		t_f		1180		
Gate Charge	V_{GS} = 4.5 V, V_{DS} = 40 V, I_D = 2.6 A (Note 3)	Q_T		4.5		nC
		Q_1		0.9		
		Q_2		2.6		
Gate Charge	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 1.5 A (Note 3)	Q_T		3.9		nC
		Q_1		1.0		
		Q_2		1.7		
SOURCE−DRAIN DIODE CHARACTERISTICS						
Forward On−Voltage	I_S = 2.6 A, V_{GS} = 0 V (Note 3) I_S = 2.6 A, V_{GS} = 0 V, T_J = 125°C	V_{SD}		0.81 0.66	1.5	V
Reverse Recovery Time	I_S = 1.5 A, V_{GS} = 0 V, dI_s/dt = 100 A/μs (Note 3)	t_{rr}		730		ns
		t_a		200		
		t_b		530		
Reverse Recovery Stored Charge		Q_{RR}		6.3		μC
ESD CHARACTERISTICS (Note 4)						
Electro−Static Discharge Capability	Human Body Model (HBM)	ESD	5000			V
	Machine Model (MM)		500			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Not subject to production testing.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

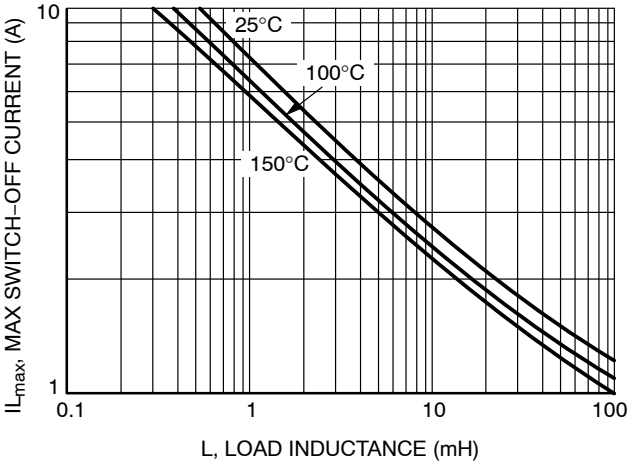


Figure 1. Single Pulse Maximum Switch−off Current vs. Load Inductance

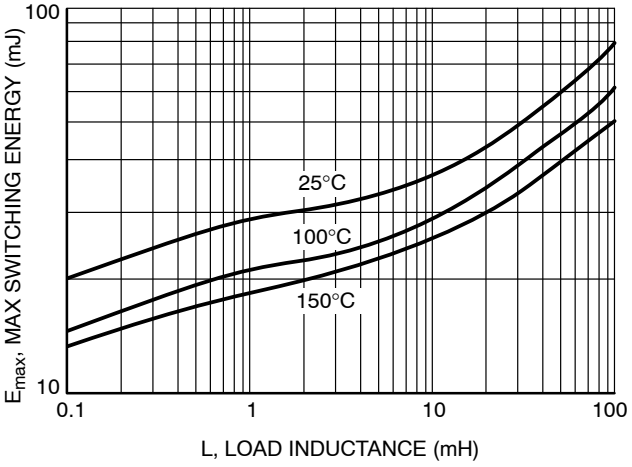


Figure 2. Single Pulse Maximum Switching Energy vs. Load Inductance

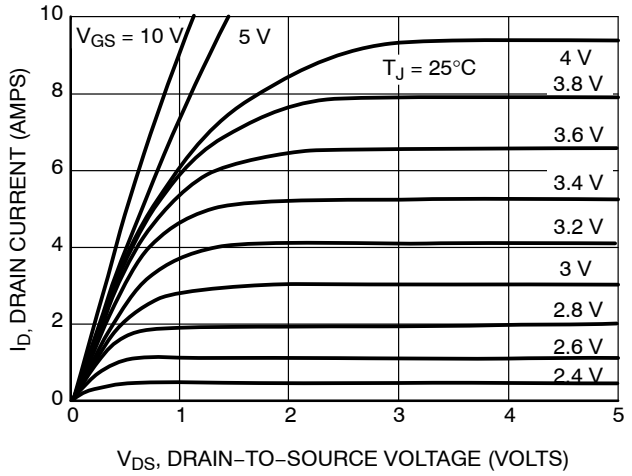


Figure 3. On−State Output Characteristics

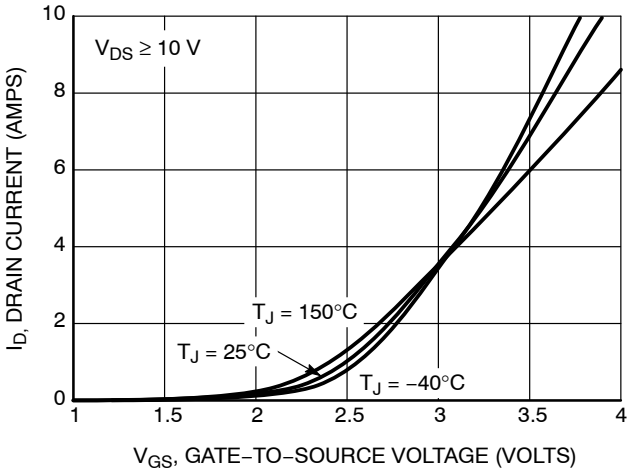


Figure 4. Transfer Characteristics

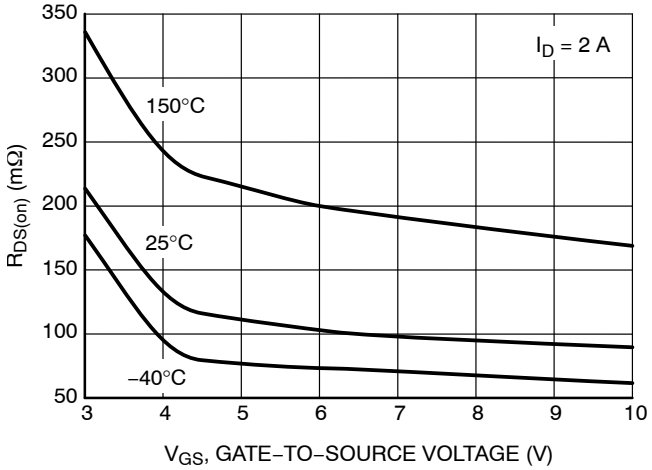


Figure 5. $R_{DS(on)}$ vs. Gate−Source Voltage

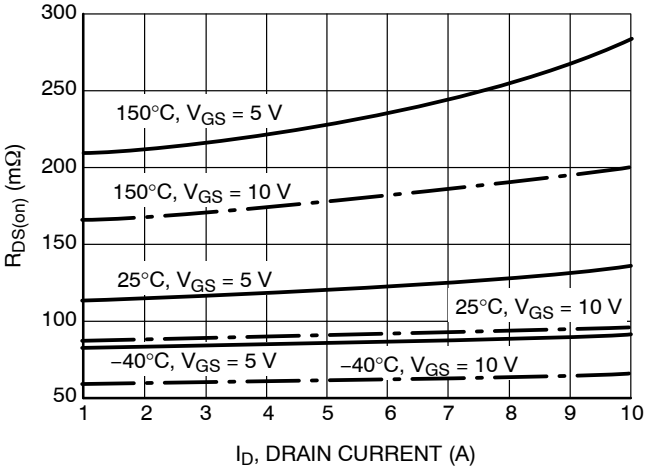


Figure 6. $R_{DS(on)}$ vs. Drain Current

TYPICAL PERFORMANCE CURVES

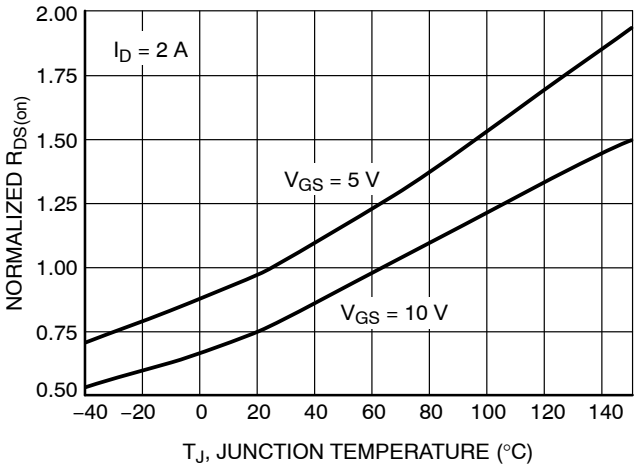


Figure 7. Normalized $R_{DS(on)}$ vs. Temperature

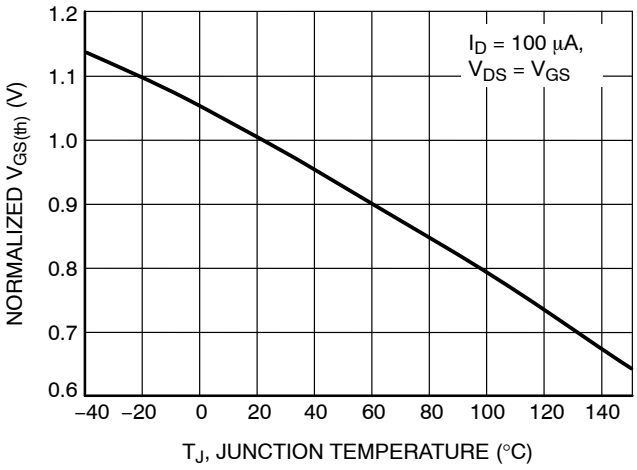


Figure 8. Normalized Threshold Voltage vs. Temperature

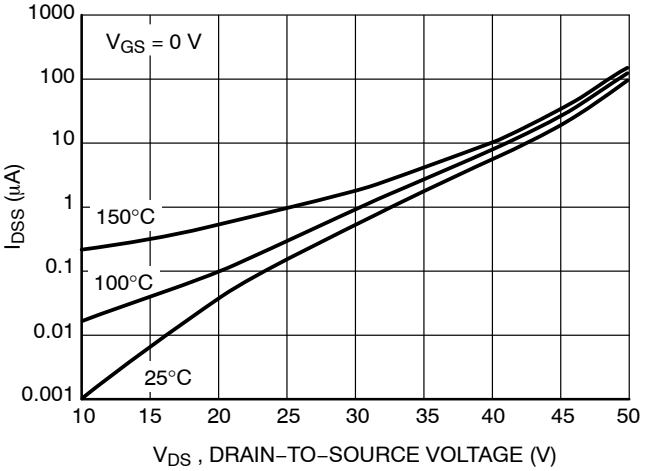


Figure 9. Drain−to−Source Leakage Current

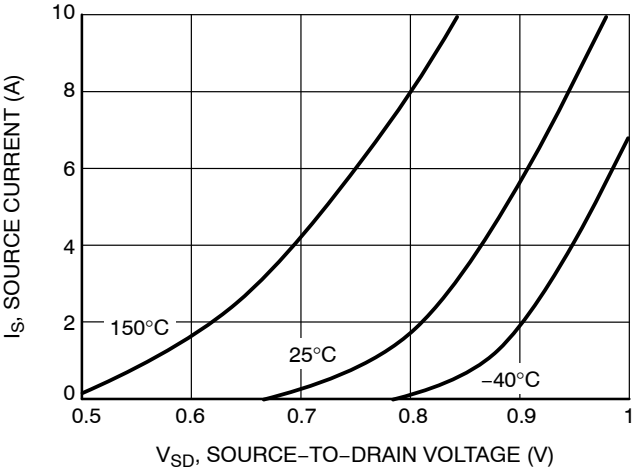


Figure 10. Source−Drain Diode Forward Characteristics

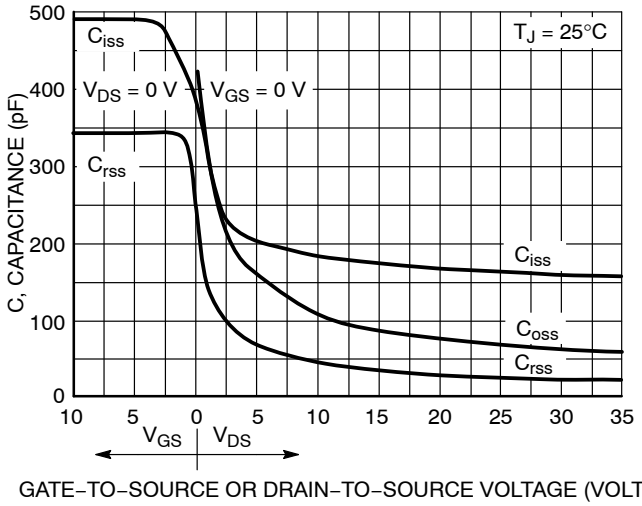


Figure 11. Capacitance Variation

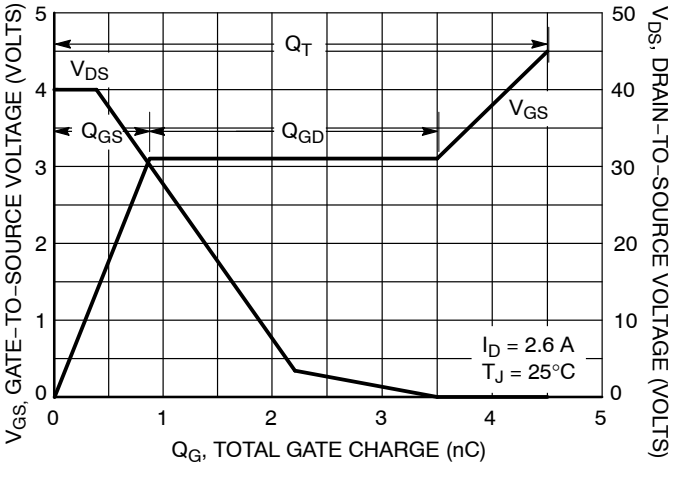


Figure 12. Gate−to−Source Voltage vs. Total Gate Charge

TYPICAL PERFORMANCE CURVES

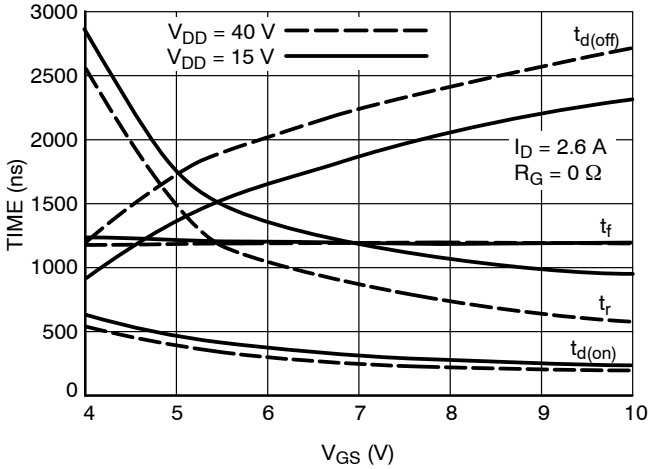


Figure 13. Resistive Load Switching Time vs. Gate−Source Voltage

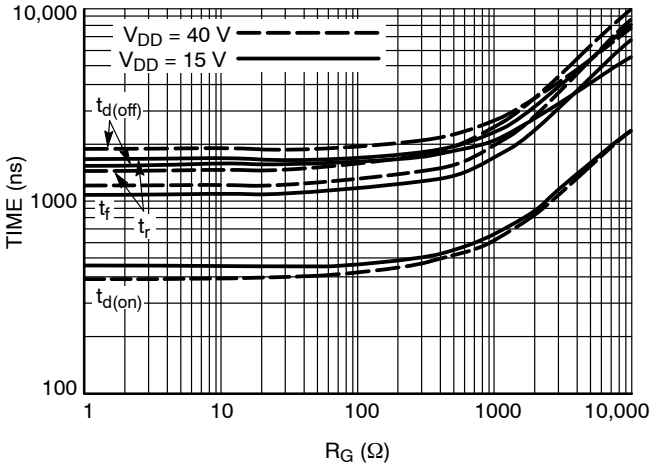


Figure 14. Resistive Load Switching Time vs. Gate Resistance (V_{GS} = 5 V, I_D = 2.6 A)

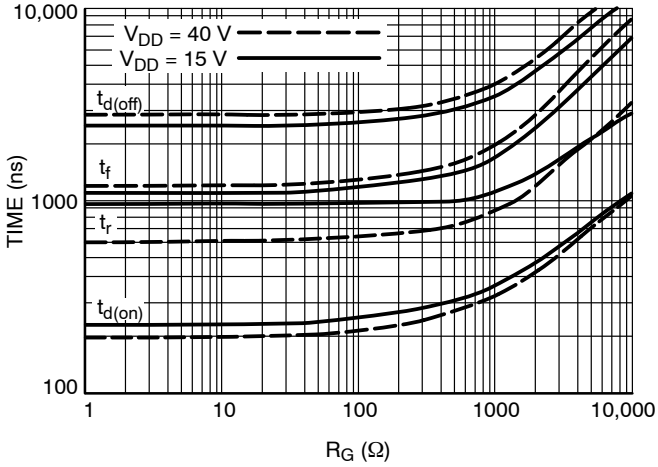


Figure 15. Resistive Load Switching Time vs. Gate Resistance (V_{GS} = 10 V, I_D = 2.6 A)

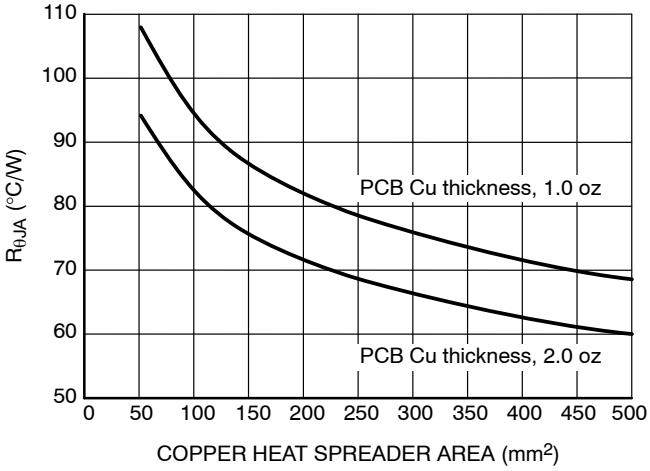


Figure 16. $R_{\theta JA}$ vs. Copper Area

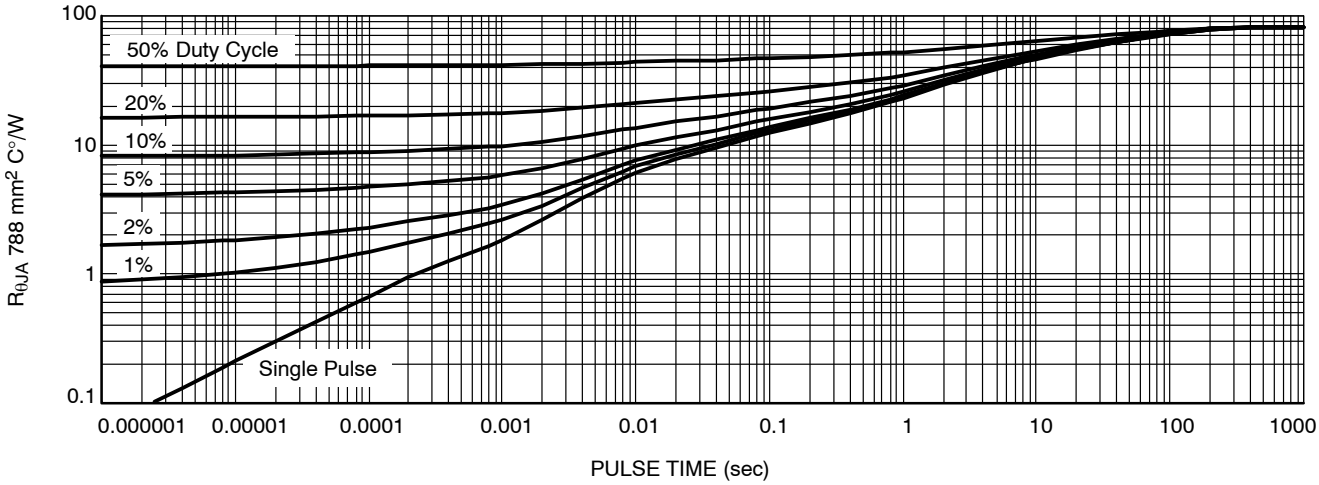


Figure 17. Transient Thermal Resistance

ORDERING INFORMATION

Device	Package	Shipping†
NCV8440STT1G	SOT−223 (Pb−Free)	1000 / Tape & Reel
NCV8440ASTT1G	SOT−223 (Pb−Free)	1000 / Tape & Reel
NCV8440STT3G	SOT−223 (Pb−Free)	4000 / Tape & Reel
NCV8440ASTT3G	SOT−223 (Pb−Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

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For additional information, please contact your local Sales Representative

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